

Curriculum Vitae

Full Name	Dr. Vijay Singh Bist			
Designation	Senior Technical Officer (Electronics)			
Department	Instrumentation Engineering-USIC			
Campus	Chauras Campus			
Telephone	01370-267888			
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Email	vs.bisht@hnbgu.ac.in ; vsb.usic.hnbgu@gmail.com. vsbist_usic68@yahoo.com;			
Education Qualification	D.Phil. (1998), HNB Garhwal University, Srinagar.			
Teaching Experience	21 Years	Research Experience	31 Years	
Areas of Interest/ Specialization				
<ol style="list-style-type: none"> 1. Basic Electrical Engineering, 2. Digital Electronics, 3. Electrical & Electronic Instrumentation and Measurements, 4. Analytical Instrumentation. 				
Honours & Awards: NIL				
Member of Academic Institutions: NIL				
Membership of Scientific Organization:				
<ol style="list-style-type: none"> 1. A life member of the Instrument Society of India. 				
Research Supervision (No. of Ph.D. Degree Awarded/ Registered): NIL				
Research Projects/ MOU undertaken: NIL				
Administrative Experience:				
<ol style="list-style-type: none"> 1. Coordinator, "B. Tech. first year". 2. Member of the "B. Tech. admissions committee". 3. Member of the "Departmental Purchase Committee". 4. Member of the "School End Semester Examination Committee". 5. Centre Superintendent, H.N.B. Garhwal University, Srinagar (Garhwal), Chauras Campus, Examination Centre for the session (2020-21). 				
Scientific Visits Abroad/International Collaboration: NIL				
Conference/Symposium/Workshop Attended during last five years (2012-2017).				
National:				
<ol style="list-style-type: none"> 1. Attendant National Conference on 'Recent Advances in Materials Science (NCRAMS)', 26 – 30 October, 2013, HNB Garhwal University, Srinagar (Garhwal). 				
Conference/Symposium/Workshop Organized during last five years (2012-2017)				
<ol style="list-style-type: none"> 1. Organized the 'World IPR day' jointly with UCOST, Dehradun at USIC, HNB Garhwal University, Srinagar (Garhwal), April 26, 2014. 				

Best Peer-Reviewed Publications 2009 onwards (up to 05)

Journals: *International Physics Research*

Proceedings: NIL

Books:

1. "Experiments in Digital Electronics", **Dr. V. S. Bist**, A. S. Bahuguna, and Dr. Sunil Semwal, Neel Kamal Prakashan, September-2021, ISBN: 978-81-952786-5-7.

Total Number of Research Publications:

1. Temperature dependence of $\langle S_q^z \rangle$ and $\langle S_q^x \rangle$, collective proton frequency width, and collective phonon frequency, in paraelectric phase of KH_2PO_4 , **V. S. Bist**, S. C. Bhatt and N. S. Panwar, *Global Journal of Science Frontier Research*, **10** (2010) 18.
2. Relaxation processes and ultrasonic attenuation in KDP - type ferroelectric, **V. S. Bist**, and N. S. Panwar, *GJSFR*, **11** (2011) 25.
3. Dielectric Properties of Order-Disorder Type Crystals, **V. S. Bist**, and N. S. Panwar, *GJSFR -Mathematics and Decision Sciences*, **12** (2012) 23.
4. Temperature Dependence of Relaxation Rate in KH_2PO_4 above T_c , **V. S. Bist**, and N. S. Panwar, *GJSFR -Physics and Space Science*, **13** (2013) 35.
5. Temperature Dependence of Inverse Dielectric Susceptibility in KDP -Type Crystals, **V. S. Bist**, and N. S. Panwar, *GJSFR - Physics and Space Science*, **13** (2013) 23.
6. Temperature dependence of dielectric loss tangent in KDP (KH_2PO_4) type crystals, **V. S. Bist**, and N. S. Panwar, *GJSFR - Physics and Space Science*, **15** (2015) 13.
7. Phase Transitions in KDP-Type crystals, **V. S. Bist**, N. S. Panwar, and B. S. Semwal, *Chemical Science Transactions*, **4(4)** (2015) 1131.
8. Relaxation time in KDP-Type ferroelectrics above T_c , **V. S. Bist**, N. S. Panwar, and B. S. Semwal, *International Journal of Emerging Technology and Advanced Engineering*, **5(10)** (2015) 317.
9. Study of Dielectric Properties and Ultrasonic Attenuation in KDP-Type Ferroelectrics, **V. S. Bist**, N. S. Panwar, *International Physics Research*, **5(10)** (2016) 9475740.
10. Soft mode dynamics of order-disorder type crystals, **V. S. Bist**, N. S. Panwar, and B. S. Semwal, *Chemical Science Transactions*, **4(4)** (2016) 1131.